

**isc Silicon NPN Power Transistor**

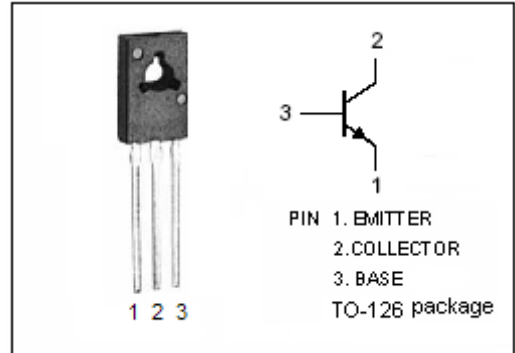
**2SC2911**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 160V(\text{Min})$
- Good Linearity of  $h_{FE}$
- High Switching Speed
- Complement to Type 2SA1209

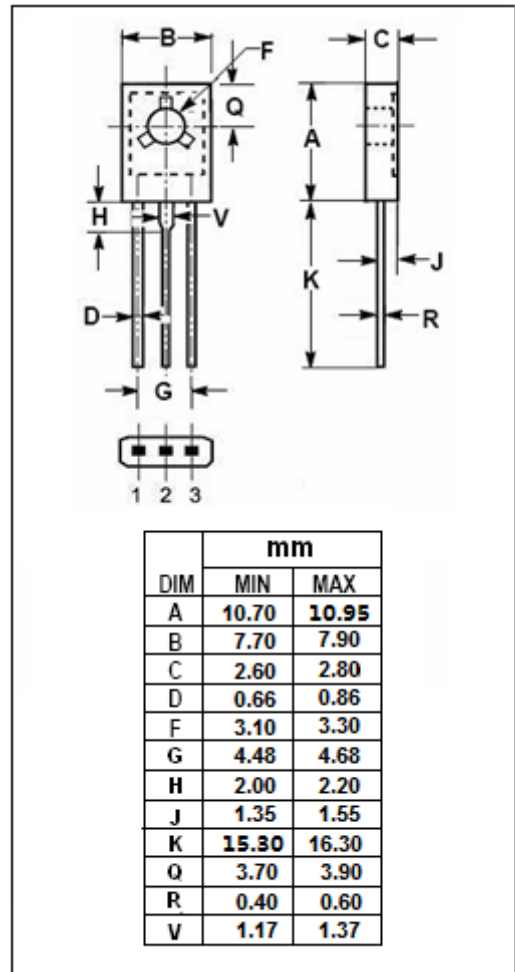
**APPLICATIONS**

- Designed for high-voltage switching and AF 100W predriver applications.



**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	140	mA
$I_{CP}$	Collector Current-Pulse	200	mA
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	10	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC2911****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=50\text{mA}; I_B=5\text{mA}$			0.3	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			0.1	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$			0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=10\text{mA}; V_{CE}=5\text{V}$	100		400	
$f_T$	Current-Gain—Bandwidth Product	$I_C=10\text{mA}; V_{CE}=10\text{V}$		150		MHz
$C_{OB}$	Collector Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1\text{MHz}$		3		pF

◆  **$h_{FE}$  Classifications**

R	S	T
100-200	140-280	200-400